

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claims 1-45 (Canceled)

Claim 46 (New): A tested semiconductor device produced by a process comprising the steps of:  
providing a wafer having a plurality of semiconductor devices thereon, each of said semiconductor devices having a plurality of electrical contact terminals;  
providing a probe card assembly, said probe card assembly comprising:  
a printed circuit board having a plurality of electrical contacts,  
a probe substrate having a plurality of interconnection elements, each interconnection element comprising a tip structure disposed at an end of said interconnection element, said tip structure comprising a blade oriented such that a length of said blade is within approximately 645 degrees of an axis parallel to a wiping motion of said tip structure,  
a compliant element disposed between said printed circuit board and said probe card for providing electrical connections between ones of said electrical contacts and ones of said interconnection elements;  
bringing said wafer and said probe card assembly into contact such that ones of said electrical contact terminals of said semiconductor devices are in wiping electrical contact with ones of said tip structure; and  
testing said semiconductor devices.

Claim 47 (New): The tested device of claim 46, wherein said tip structure is integrally formed with said interconnection element.

Claim 48 (New): The tested device of claim 46, wherein said interconnection element comprises a buckling beam probe.

Claim 49 (New): The tested device of claim 46, wherein said interconnect element is resilient.

Claim 50 (New): The tested device of claim 46, wherein said blade is oriented such that a length of said blade is within approximately 630 degrees of an axis parallel to said wiping motion of said tip structure.

Claim 51 (New): The tested device of claim 50, wherein said blade is oriented such that a length of said blade is within approximately 615 degrees of an axis parallel to said wiping motion of said tip structure.

Claim 52 (New): The tested device of claim 46, wherein said blade comprises a sharpened edge along said length thereof.

Claim 53 (New): The tested device of claim 46, wherein said tip structure comprises at least one of palladium, cobalt, rhodium, tungsten, or diamond.

Claim 54 (New): The apparatus of claim 46, wherein said tip structure comprises a material comprising a spring alloy.

Claim 55 (New): The tested device of claim 46, wherein said tip structure is secured to said interconnection element by one of braze or solder.

Claim 56 (New): A tested semiconductor device produced by a process comprising the steps of:

- providing a wafer having a plurality of semiconductor devices thereon, each of said semiconductor devices having a plurality of electrical contact terminals;
- providing a probe card assembly, said probe card assembly comprising:
  - a printed circuit board having a plurality of electrical contacts,
  - a probe substrate having a plurality of interconnection elements, each interconnection element comprising a tip structure disposed at an end of said interconnection element, said tip structure comprising a blade oriented on the interconnection element such that said length of said blade runs substantially parallel to a horizontal wiping motion of said blade,
  - a compliant element disposed between said printed circuit board and said probe card for providing electrical connections between ones of said electrical contacts and ones of said interconnection elements;
- moving said wafer into contact with said probe card assembly such that ones of said electrical contact terminals of said semiconductor devices are in wiping electrical contact with ones of said tip structure; and
- testing said semiconductor devices.

Claim 57 (New): A tested semiconductor device produced by a process comprising the steps of:

- providing a semiconductor device having a plurality of electrical contact terminals;
- providing an interface board, said interface board comprising a probe substrate having a plurality of interconnection elements, each interconnection element comprising a tip structure disposed at an end of said interconnection element, said tip structure comprising a blade oriented on the interconnection element such that said length of said blade runs substantially parallel to a horizontal wiping motion of said blade;
- bringing said semiconductor device and said interface board into contact such that ones of said electrical contact terminals of said semiconductor device are in wiping electrical contact with ones of said tip structure; and
- testing said semiconductor device.